

CLAIMS

What is claimed is:

1. A method comprising:
over an area of a substrate, forming a plurality of three dimensional first structures;
following forming the first structures, conformally introducing a sacrificial material over the area of the substrate;
introducing a second structural material over the sacrificial material; and
removing the sacrificial material.
2. The method of claim 1, prior to removing the sacrificial material, further comprising exposing a portion of the sacrificial material.
3. The method of claim 2, wherein exposing a portion of the sacrificial material comprises removing a portion of the second structural material.
4. The method of claim 1, prior to introducing the second structural material, further comprising patterning the sacrificial material.
5. The method of claim 1, wherein the first structural material comprises silicon and the sacrificial material comprises silicon dioxide and introducing the sacrificial material comprises growing.
6. The method of claim 1, wherein removing the sacrificial material comprises suspending the second structural material as a second structure coupled to the first structures.
7. The method of claim 1, wherein patterning the first structures defines a plurality of first areas of the portion of the substrate occupied by the first structures and at least a second area of the portion of the substrate free of the first structures, and introducing the sacrificial material comprises introducing the sacrificial material at least over the second area.

8. A method comprising:
over an area of a surface of a substrate, lithographically patterning a plurality of first structures, the plurality of first structures having a first dimension about the surface of the substrate and a second different dimension;
following forming the first structures, conformally introducing a sacrificial material layer over the area of the substrate;
forming second structures over the sacrificial material; and
removing the sacrificial material.
9. The method of claim 8, prior to forming second structures, further comprising patterning the sacrificial material.
10. The method of claim 8, prior to removing the sacrificial material, further comprising exposing a portion of the sacrificial material.
11. The method of claim 9, wherein exposing a portion of the sacrificial material comprises removing a portion of the second structural material.
12. The method of claim 8, wherein the sacrificial material comprises silicon dioxide and introducing the sacrificial material comprises growing.
13. The method of claim 8, wherein removing the sacrificial material comprises suspending the second structures by the first structures.
14. An apparatus comprising:
a first structure on a substrate; and
a second structure on the substrate and separated from the first structure by an unfilled gap defined by the thickness of a removed film.
15. The apparatus of claim 14, further comprising a plurality of third structures, wherein the second structure is suspended between the plurality of third structures.

- [illegible]